Taller vs. Smaller:

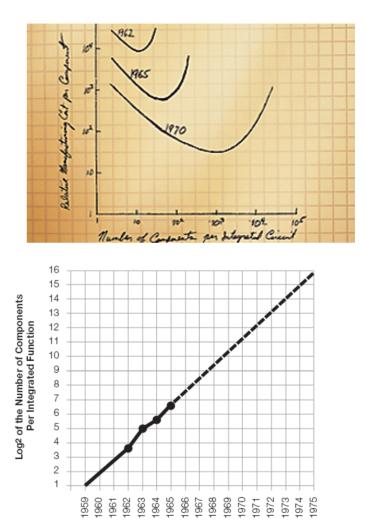
3D Development & Moore's Law

F. M. Schellenberg, Ph.D. Design-to-Silicon Division Mentor Graphics

GRC ETAB Summer Study La Quinta, CA June 30, 2009



- Famous 1965 article
- Observation on COST
 - Cost per component decreases with integration
- Number of transistors doubles every 2 years

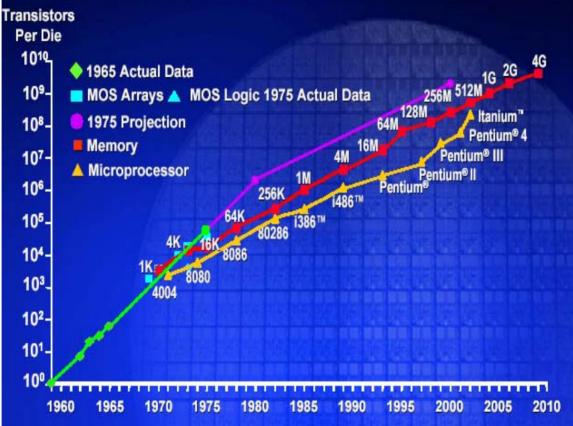


Cramming More Components onto Integrated Circuits G. Moore, Electronics Vol. 38, pp. 114-117 (1965)

http://download.intel.com/museum/Moores_Law/Articles-Press_Releases/Gordon_Moore_1965_Article.pdf Year



Integrated Circuit Complexity



Source: Intel

ftp://download.intel.com/research/silicon/Gordon_Moore_ISSCC_021003.pdf

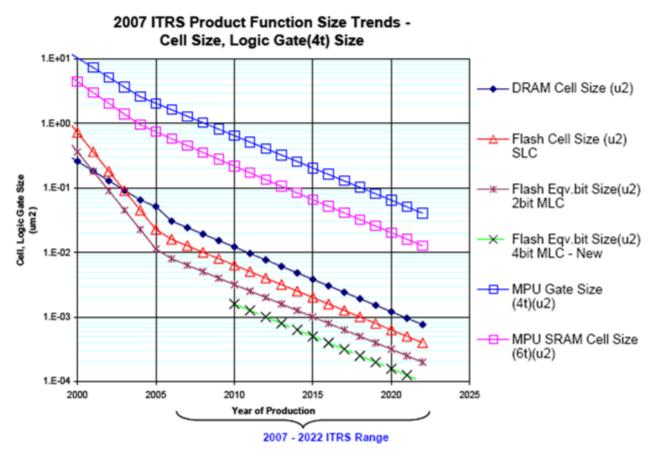


Achieved by shrinking

- **Smaller feature sizes (linear dimension)**
- **Smaller Cell sizes (aerial dimension)**
- "Smaller" Chip sizes (for same function)
 - Improves yield for a fixed wafer size
- Other aspects also shrink
 - **Voltage**
 - **Oxide layers**
- All now planned in the ITRS Meetings
 - www.itrs.net



Moore's Law: ITRS

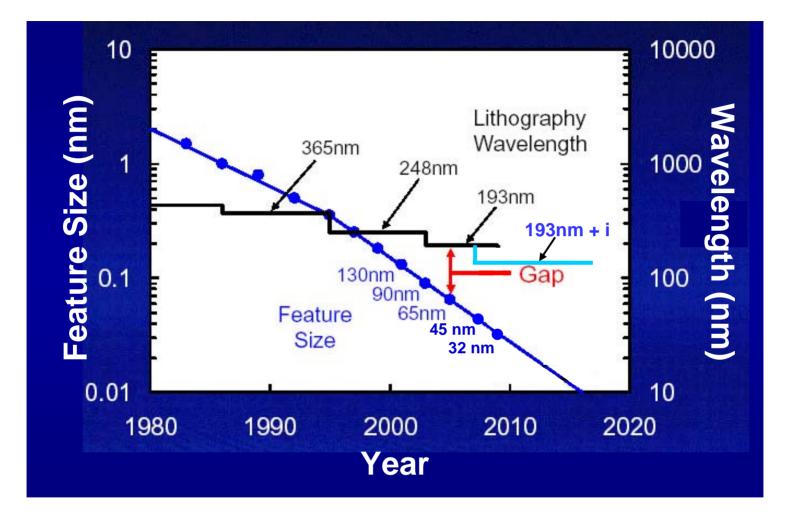


 ITRS 2008 Update
 Figure ORTC3
 ITRS Product Technology Trends:

 http://www.itrs.net
 Product Functions/Chip and Industry Average "Moore's Law" Trends--Updated



Moore's Law: Subwavelength



Adapted from: M. Bohr, http://www.intel.com/technology/silicon/65nm_technology.htm



Litho Scaling Gap

- **Gap created opportunity**
 - Shrinking Paradigm changed
- Emergence of RET
 - **Resolution Enhancement Technology**
 - Modeling sub-wavelength behavior/distortions
 - Adapting IC Designs/Layouts to compensate
 - OPC
 - Phase Shifting Mask
 - Off-Axis Illumination
 - Immersion (High NA)
 - Double Patterning
 - SMO (source/Mask Optimization)



RET adds complexity

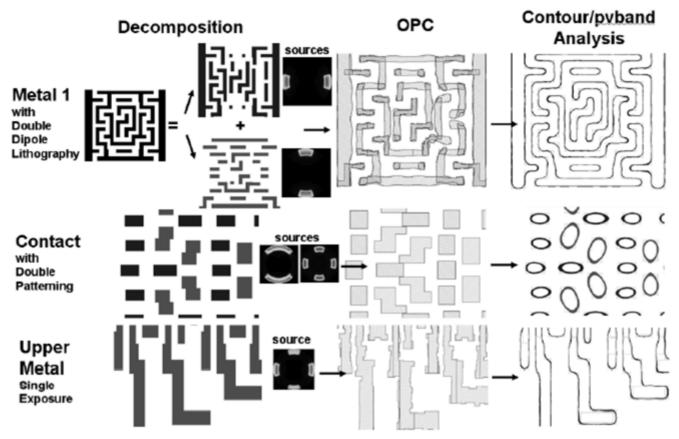
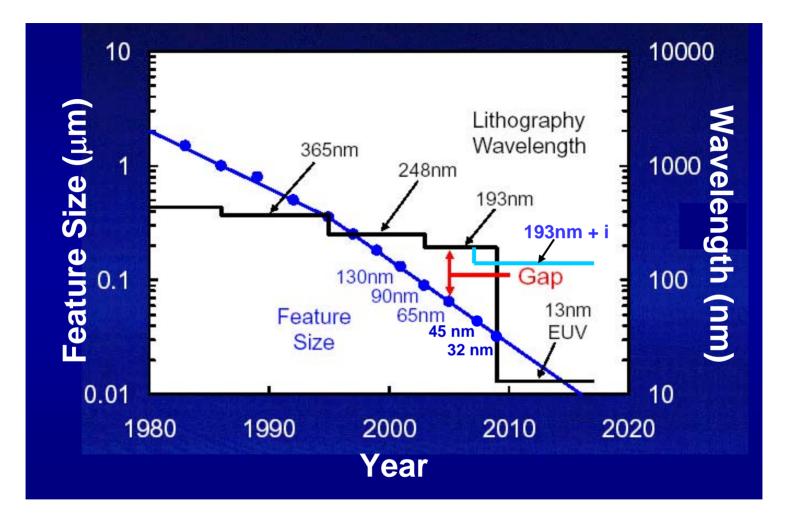


Figure 3. The experimental flow for decomposing, applying OPC, generating post-OPC contours, and analysis is shown. For our experiments, we studied the Metal 1, Contact, and Upper Metal processes.

Inverse vs. traditional OPC for the 22nm node

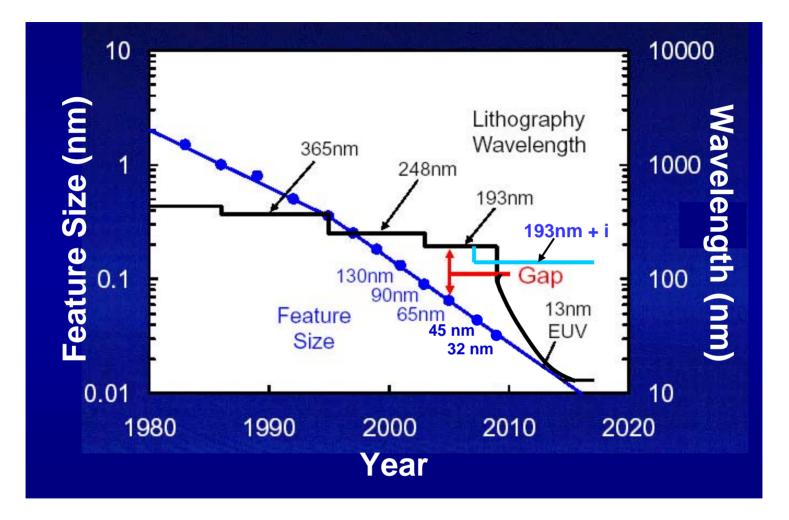
James Word et al., Mentor Graphics, Proc. SPIE 7274, 72743A (2009)





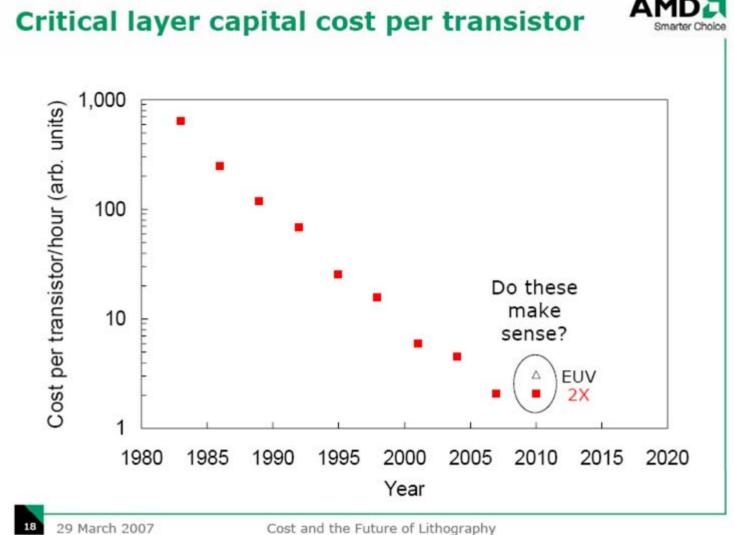
Adapted from: M. Bohr, http://www.intel.com/technology/silicon/65nm_technology.htm





Adapted from: M. Bohr, http://www.intel.com/technology/silicon/65nm_technology.htm





Source: H. Levinson, SEMI Silicon Valley Lunch Forum, 3-29-2007 http://content.semi.org/cms/groups/public/documents/events/p041431.pdf





Lessons Learned

Litho scaling running out of steam

- Complexity and Cost problems
- <u>not</u> technology barriers
- The Gap has been filled with Modeling Tools
 RET/DFM Market now ~\$500M/ year
- Expect more ITRS revisions
 - New consumer devices don't need shrinking
 - All exponentials eventually end
- The End of the Roadmap (as we know it) is near!



What's Next

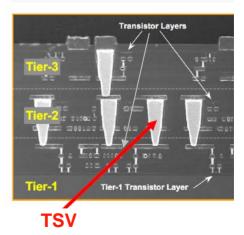
• Nowhere to go but UP.



Stacking: What can be achieved

- Stacking creates more functions per cm²
 - High value for cell phones, handheld devices
 - Mix-and-match of established (working) ICs
 - Memory on top of logic
- Up until now, a packaging problem
 - Like a 3-D printed circuit board
 - Wire bonding
 - Flip chips
- Thru Silicon Vias (TSVs) emerged in MEMS
 - Already a long way up the learning curve
 - Shorter wires = faster interconnects
 - Signal never "leaves" the IC
 - Integrated connections = smaller footprint



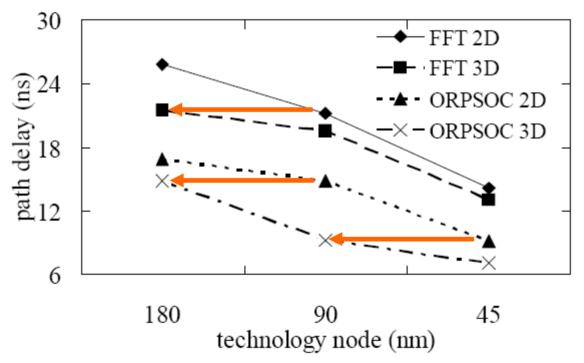




Stacking improves performance

"Stacking buys you 2 nodes"

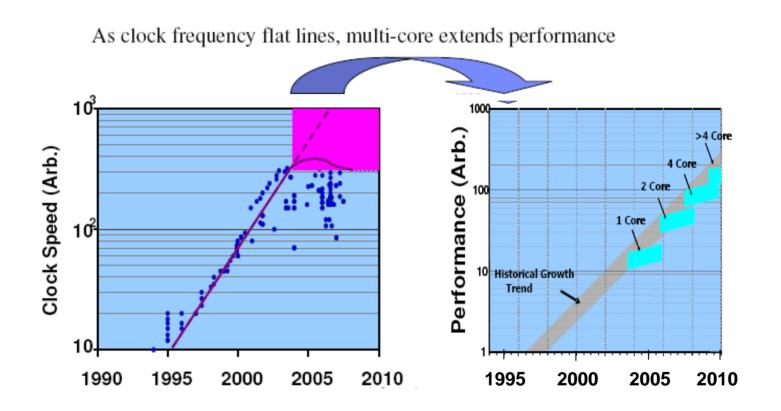
Timing



Source: P. Franzon et al, NCSU, "Design and CAD for 3D Integrated Circuits", Proceedings DAC 2008, pp. 668 – 673.



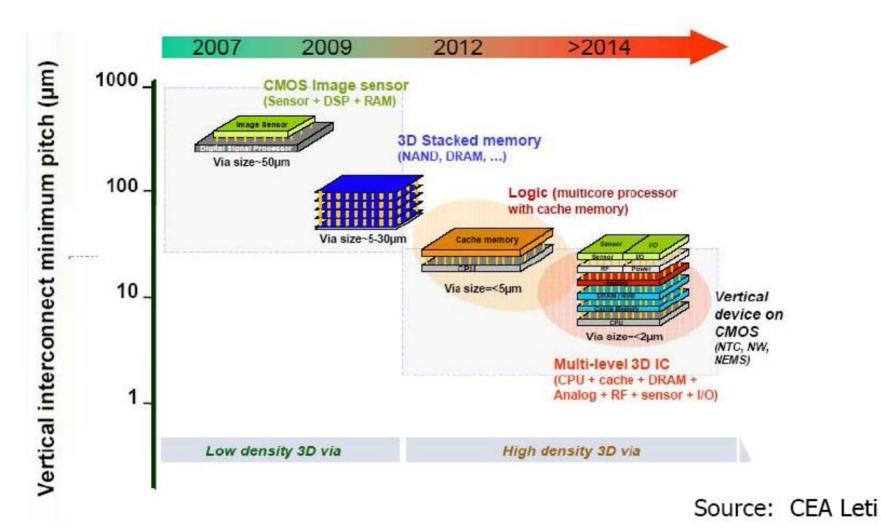
There is a Gap



Adapted from: M. Shapiro, IBM, RTI 3D Architectures for Semiconductor Integration Seminar, Nov. 2008



There is a Roadmap





3D TSV Appeal

- Higher overall density
 - Moore's Law continues
- Lower cost
 - If it yields
- Mix and match
 - Segregation of tasks
 - Logic below, memory above
 - Attach MEMS / Optoelectronics / AMS / RF / etc.



3D TSV Appeal

- Higher overall density
 - How much can you cram together?
- Lower cost
 - **Electrical Properties / failure modes of real TSV**
- Mix and match
 - Can you do it?
 - Can you design it?

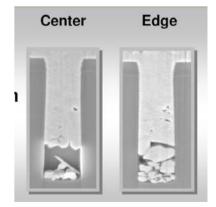


TSV Problems

- Electrical properties of the TSV itself
 - e.g. 50 μm deep, 10 μm across, Cu in insulator in Si
 - How closely spaced?
 - Can design rules do it?
 - What are L,R,C as dimensions vary?

... over time?

- Can look-up tables do the job?
- Like RET modeling problem Rule vs. model vs. hybrid
- What are the failure modes?
- Need: Reliable, adaptable compact models
- Need: Metrology basis set for calibration
- Need: Test techniques for fabricated vias



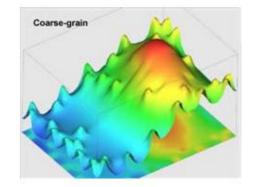


Transistors in 3D Context

- Leakage Current not gone
 - Generates heat
 - Upper layers far from the package heat sink
- Does it Matter?
 - Effect on transistors
 - **Temperature**

Need: Workable models

Stress



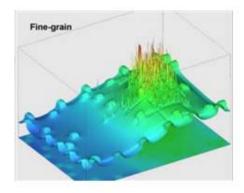


Illustration from the Gradient Design Automation www.gradient-da.com

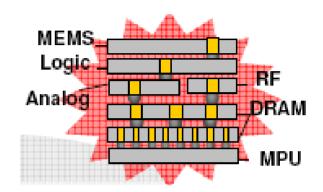


Design problems

Greatest appeal: Modularity

- Stack old memory with new logic
- Stack RF on Digital
- Stack anything on everything
 - Allow components to be made with optimal processes
- Need: What makes sense?
 - Where are the greatest benefits?
 - **Which architectures are most complementary?**





Final Slide

Market needs are the real issue

- **What can stacking do better / cheaper / faster?**
- Can it really provide 2 nodes of value?
- Modeling tools that fill the gap are needed

And provide good University projects

- Electrical properties and dependencies of vias
- **Behavior of stacked transistors**
 - Power Management
 - Temperature modeling
 - Stress modeling
- Mixed device architecture optimization



Thank you for your attention.



